



TO-92 Plastic-Encapsulate Transistors

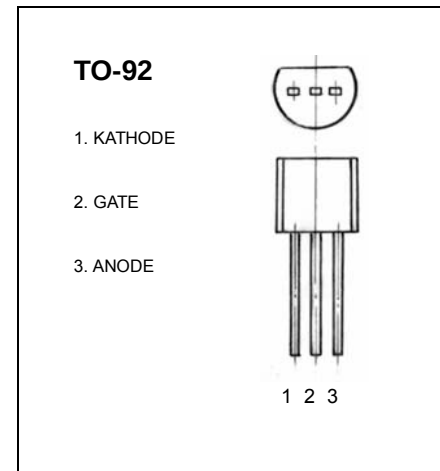
MCR 100- 6, - 8 Silicon Planar PNP Thyristor

FEATURES

Current- I_{GT} :	200	μA
I_{TRMS} :	0.8	A
V_{DRM} :	MCR100-6:	400 V
	MCR100-8:	600 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to +150°C



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
On state voltage *	V_{TM}	$I_{TM}=1A$		1.7	V
Gate trigger voltage	V_{GT}	$V_{AK}=7V$		0.8	V
Peak Repetitive forward and reverse blocking voltage MCR100-6 MCR100-8	V_{DRM} AND V_{RRM}	$I_{DRM}=10\mu A, V_{MAX}=1010V$	400 600		V
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}	$V_{AK}= \text{Rated}$ V_{DRM} or V_{RRM}		10	μA
Holding current	I_H	$I_{HL}=20mA, A_v=7V$		5	mA
Gate trigger current	I_{GT}	$V_{AK}=7V$	5	15	μA
			15	30	μA
			30	80	μA
			80	200	μA

* Forward current applied for 1 ms maximum duration, duty cycle $\leq 1\%$.

Typical Characteristics

MCR100-6,-8

FIGURE 1 – MCR100-8 CURRENT DERATING
(REFERENCE: CASE TEMPERATURE)

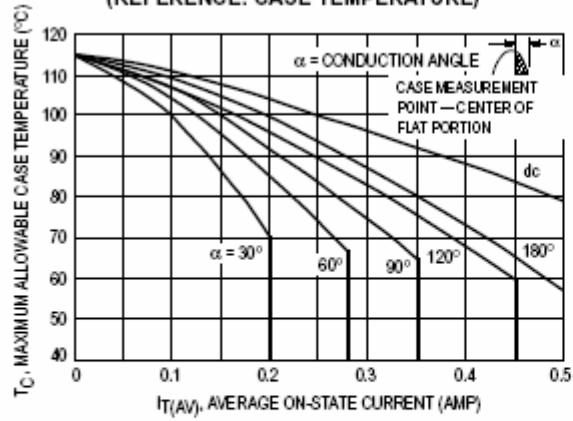


FIGURE 2 – MCR100-8 CURRENT DERATING
(REFERENCE: AMBIENT TEMPERATURE)

